



Form 1449\*

Atty. Docket No.: 303.355US4

Serial No. Unknown

INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(Use several sheets if necessary)

Applicant: Leonard Forbes et al.

Filing Date: Herewith

Group: Unknown

## U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
TD	4,113,515	09/12/1978	Kooi, E., et al.	148	1.5	03/29/76
TD	4,460,670	07/01/1984	Ogawa, et al.	430	57	11/19/82
TD	4,462,150	07/31/1984	Nishimura, H., et al.	29	576 B	09/16/82
TD	4,507,673	03/26/1985	Aoyama, M., et al.	357	23 R	09/21/83
TD	4,657,699	04/01/1987	Nair	252	513	12/17/84
TD	4,738,729	04/01/1988	Yoshida, et al.	136	258	01/27/87
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TD	4,841,349	06/20/1989	Nakano, M.	357	30	10/28/87
TD	4,849,797	07/18/1989	Ukai, Y., et al.	357	237	01/20/88
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TD	5,111,430	05/05/1992	Morie	365	185	06/21/90
TD	5,145,741	09/01/1992	Quick	428	402	02/28/91
TD	5,235,195	08/10/1993	Tran, N.T., et al.	257	59	10/19/92
TD	5,260,593	11/09/1993	Lee, R.P.	257	316	12/10/91
TD	5,293,560	03/08/1994	Harari, E.	365	185	11/03/92
TD	5,298,796	03/29/1994	Tawel, P.	307	201	07/08/92
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TD	5,388,069	02/07/1995	Kokubo, M.	365	185	03/18/93
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TD	5,449,941	09/12/1995	Yamazaki, S., et al.	257	411	10/27/92
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TD	5,465,249	11/07/1995	Cooper, et al.	365	149	11/26/91
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Examiner

Theresa J. Brown

Date Considered

12/04/01

\*Substitute Disclosure Statement Form PTO-1449.

\*\*EXAMINER: Initial is division considered whether or not division is in the same class. If not, the division is in the same class as the parent application. If the division is in the same class as the parent application, the division is in the same class as the parent application. If the division is in the same class as the parent application, the division is in the same class as the parent application.

Form 1449*	Atty. Docket No.: 303.355US4	Serial No. <u>Unknown</u> <i>09/883,795</i>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al. <i>09/883,795</i>	
	Filing Date: Herewith	Group: <u>Unknown</u> <i>254</i>

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TD	03-222367	10/01/1991	Japan	H01L	29/784	
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TD	06-224431	08/12/1994	Japan	H01L	29/784	
TD	06-302828	10/28/1994	Japan	H01L	29/788	
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Examiner <i>Thompson</i>	Date Considered <i>12/04/01</i>
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\*\*EXAMINER Initial of citation is considered whether or not citation is in accordance with MPEP 2144. When the citation is in accordance with MPEP 2144, the citation is considered to be in accordance with MPEP 2144. When the citation is not in accordance with MPEP 2144, the citation is considered to be in accordance with MPEP 2144.

Form 1449*	Atty. Docket No.: 303.355US4	Serial No. Unknown
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## FOREIGN PATENT DOCUMENTS

Examiner Initial	Invention Number No	Date	Country	Class	Subclass	Translation	
						Yes	No
70	63-181473	07/26/1988	Japan	HO1L	29/78		
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70	Benjamin, M., et al., "UV Photoemission Study of Heteroepitaxial AlGaIn Films Grown on 6H-SiC", <u>Applied Surface Science</u> , 104/105, 458-460, (1996)
70	Bermudez, V., et al., "The Growth and Properties of Al and AlN Films on GaN(0001) (1 x 1)", <u>J. Applied Physics</u> , 79, 110-119, (Jan. 1996)

Examiner <i>Theresa Brown</i>	Date Considered <i>12/12/96</i>
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\*Substitute Disclosure Statement Form PTO 1449

\*\*EXAMINER: Initial if citation considered whether or not citation is in compliance with MPEP 2112. Draw line through citation if not in compliance and not considered. Include copy of this form with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.355US4	Serial No. Unknown
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	Filing Date: Herewith	Group: Unknown

## OTHER DOCUMENTS

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TD	Friedrichs, P., et al., "Interface Properties of Metal-Oxide-Semiconductor Structures on N-Type 6H and 4H-SiC", <u>J. Applied Physics</u> , 79, 7814-7819, (May 15, 1996)
TD	Fujii, T., et al., "Bonding Structures in Highly Photoconductive a-SiC:H Films Deposited by Hybrid-Plasma Chemical Vapor Deposition", <u>Journal of Non-Crystalline Solids</u> , 198-200, 577-581, (1996)
TD	Goetzberger, A., et al., <u>Applied Solid State Science: Advances in Materials and Device Research</u> , R. Wolfe, ed., Academic Press, New York, Including pg. 233, (1969)
TD	Graul, J., et al., "Growth Mechanism of Polycrystalline beta-SiC Layers on Silicon Substrate", <u>Applied Phys. Lett.</u> , 21, 67-69, (July 1972)
TD	Hamakawa, Y., et al., "Optoelectronics and Photovoltaic Applications of Microcrystalline SiC", <u>Materials Research Society Symposium Proceedings</u> , 164, Boston, MA, 291-301, (11/29-12/1, 1989)
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TD	Hu, G., et al., "Will Flash Memory Replace Hard Disk Drive?", <u>1994 IEEE International Electron Device Meeting</u> , Panel Discussion, Session 24, Outline, 2 pages, (Dec. 1994)
TD	Hwang, J., et al., "High Mobility beta-SiC Epilayer Prepared by Low-pressure Rapid Thermal Chemical Vapor Deposition on a (100) Silicon Substrate", <u>Thin Solid Films</u> , 272, 4-6, (1996)
TD	Hybertsen, M.S., "Absorption and Emission of Light in Nanoscale Silicon Structures", <u>Phys. Rev. Lett.</u> , 72, 1514-1517, (1994)
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TD	Kato, M., et al., "Read-Disturb Degradation Mechanism due to Electron Trapping in the Tunnel Oxide for Low-voltage Flash Memories", <u>IEEE Electron Device Meeting</u> , 45-48, (1994)
TD	Kothandaraman, M., et al., "Reactive Ion Etching of Trenches in 6H-SiC", <u>J. Electronic Materials</u> , 25, 875-878, (1996)

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\*Substitute Disclosure Statement Form "PTO 1449"

\*\*EXAMINER: Initial if citation considered; whether or not citation is in accordance with MPEP 2.101. If not in accordance and not considered, include copy of this form with next communication to applicant.

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Group: Unknown

## OTHER DOCUMENTS

\*\*Examiner  
Initial

Including Author, Title, Date, Pertinent Pages, Etc.:

10	Maury, F., et al., "Chemical Vapor Co-Deposition of C and SiC at Moderate Temperature for the Synthesis of Compositionally Modulated Si(x)C(1-x) Ceramic Layers", <u>Surface and Coatings Technology</u> , 76-77, 119-125, (1995)
70	McLane, G., et al., "High Etch Rates of SiC in Magnetron Enhanced SF(6) Plasmas", <u>Applied Phys. Lett.</u> , 68, 3755-3757, (June 1996)
70	Mogab, C., et al., "Conversion of Si to Epitaxial SiC by Reaction with C(2)H(2)", <u>J. Applied Physics</u> , 45, 1075-1084, (March 1974)
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70	Muller, K., et al., "Trench Storage Node Technology for Gigabit DRAM Generations", <u>Digest IEEE International Electron Devices Meeting</u> , San Francisco, CA, 507-510, (Dec. 1996)
70	Nemanich, P., et al., "Diamond Negative Electron Affinity Surfaces, Structures and Devices", <u>Proc. : Third International Conference on Applications of Diamond Films and Related Materials</u> , 1, Gaithersburg, MD, 17-24, (1995)
70	Nemanich, R., et al., "Negative Electron Affinity Surfaces of Aluminum Nitride and Diamond", <u>Diamond and Related Materials</u> , 5, 790-796, (1996)
70	Ouyang, M., et al., "Deposition of Diamond-Like Carbon Films via Excimer Laser Ablation of Polybutadiene", <u>Materials Science and Engineering</u> , B39, 228-231, (1996)
10	Pankove, J., "Photoelectric Emission", <u>In: Optical Processes in Semiconductors</u> , Dover Publications Inc., New York, 287-301, (1971)
70	Pankove, J., et al., "Photocmission from GaN", <u>Applied Phys. Lett.</u> , 25, 53-55, (1974)
70	Papadas, C., et al., "Modeling of the Intrinsic Retention Characteristics of FLOTOX EEPROM Cells Under Elevated Temperature Conditions", <u>IEEE Transaction on Electron Devices</u> , 42, 678-682, April 1995

Examiner

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\*Substitute Disclosure Statement Form 1449-1449.

\*\*EXAMINER: Initial if citation considered; otherwise, do not. If citation is in accordance with MPEP 21.12, draw line and indicate if not in accordance and not considered. Include copy of this form with next communication to applicant.